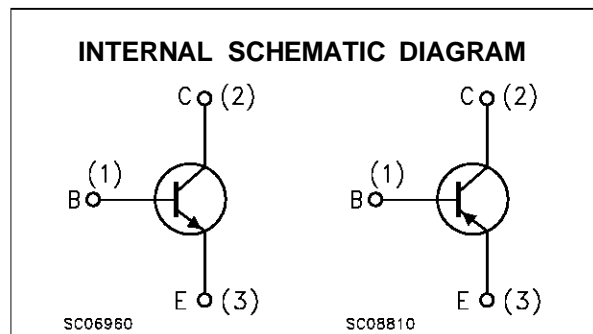
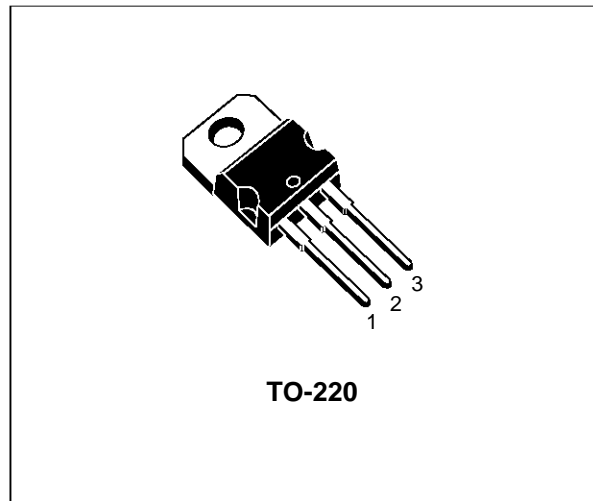


COMPLEMENTARY SILICON POWER TRANSISTORS

- BD534, BD535, BD536, BD537 AND BD538 ARE SGS-THOMSON PREFERRED SALESTYPES

DESCRIPTION

The BD533, BD535, and BD537 are silicon epitaxial-base NPN power transistors in Jedec TO-220 plastic package, intended for use in medium power linear and switching applications. The complementary PNP types are BD534, BD536, and BD538 respectively.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value			Unit	
		NPN	BD533	BD535		BD537
		PNP	BD534	BD536		BD538
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	45	60	80	V	
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	45	60	80	V	
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	45	60	80	V	
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	5			V	
I_C, I_E	Collector and Emitter Current	8			A	
I_B	Base Current	1			A	
P_{tot}	Total Dissipation at $T_c \leq 25^\circ C$	50			W	
T_{stg}	Storage Temperature	-65 to 150			$^\circ C$	
T_j	Max. Operating Junction Temperature	150			$^\circ C$	

For PNP types voltage and current values are negative.

BD533/BD534/BD535/BD536/BD537/BD538

THERMAL DATA

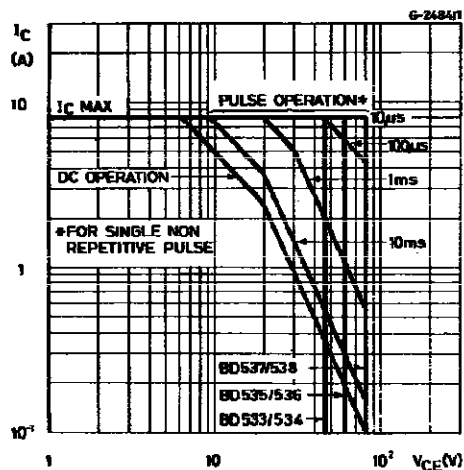
R _{thj-case}	Thermal Resistance Junction-case	Max	2.5	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	70	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	for BD533/534 V _{CB} = 45 V for BD535/536 V _{CB} = 60 V for BD537/538 V _{CB} = 80 V			100 100 100	μA μA μA
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	for BD533/534 V _{CE} = 45 V for BD535/536 V _{CE} = 60 V for BD537/538 V _{CE} = 80 V			100 100 100	μA μA μA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA	for BD533/534 45 for BD535/536 60 for BD537/538 80			V V V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 2 A I _C = 6 A	I _B = 0.2 A I _B = 0.6 A	0.8	0.8	V V
V _{BE*}	Base-Emitter Voltage	I _C = 2 A	V _{CE} = 2 V		1.5	V
h _{FE*}	DC Current Gain	I _C = 10 mA I _C = 500 mA I _C = 2 A	V _{CE} = 5 V for BD533/534 for BD535/536 for BD537/538 V _{CE} = 2 V V _{CE} = 2 V for BD533/534 for BD535/536 for BD537/538	20 20 15 40 25 25 15		
f _T	Transition frequency	I _C = 500 mA	V _{CE} = 1 V	3	12	MHz

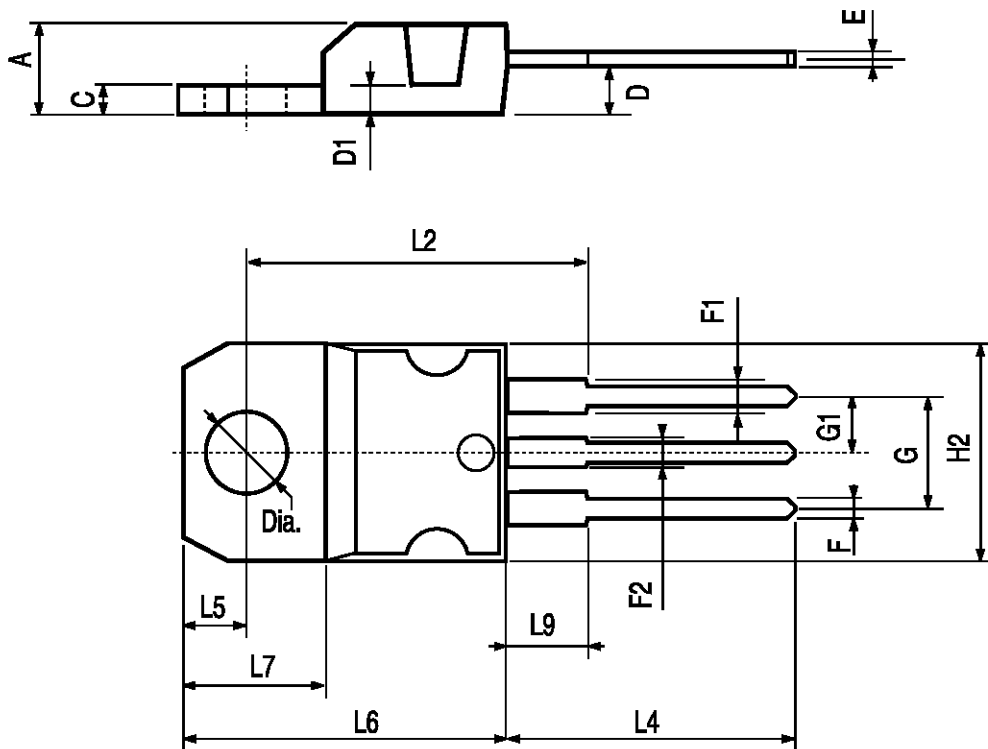
* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %
For PNP types voltage and current values are negative.

Safe Operating Areas



TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



P011C

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